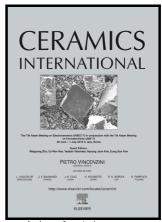
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vww.elsevier.com/locate/ceri

PII: S0272-8842(17)32534-8

DOI: https://doi.org/10.1016/j.ceramint.2017.11.079

CERI16734 Reference:

To appear in: Ceramics International

Received date: 20 October 2017 Revised date: 9 November 2017 Accepted date: 11 November 2017

Cite this article as: Daqiang Hu, Ying Wang, Shiwei Zhuang, Xin Dong, Yuantao Zhang, Jingzhi Yin, Baolin Zhang, Yuanjie Lv, Zhihong Feng and Guotong Du, Surface morphology evolution and optoelectronic properties of heteroepitaxial Si-doped β-Ga₂O₃ thin films grown by metal-organic chemical vapor deposition, Ceramics International, https://doi.org/10.1016/j.ceramint.2017.11.079

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ACCEPTED MANUSCRIPT

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